



#### REVISION HISTORY

| <u>Revision</u> | <u>Description</u>                                                                                                                                                                                                                                                                                                                                                                                                                    | <u>Issue Date</u> |
|-----------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------------|
| Rev. 1.0        | Initial Issue                                                                                                                                                                                                                                                                                                                                                                                                                         | Apr.28.2006       |
| Rev. 1.1        | Revised Package Outline Dimension(TSOP-II)                                                                                                                                                                                                                                                                                                                                                                                            | Apr.12.2007       |
| Rev. 1.2        | Revised $V_{\text{TERM}}$ to $V_{\text{T1}}$ and $V_{\text{T2}}$<br>Revised Test Condition of $I_{\text{CC}}/I_{\text{SB1}}/I_{\text{DR}}$<br>Revised <b>FEATURES &amp; ORDERING INFORMATION</b><br><b><u>Lead free and green package available</u></b> to <b><u>Green package available</u></b><br>Deleted $T_{\text{SOLDER}}$ in <b><u>ABSOLUTE MAXIMUM RATINGS</u></b><br>Added packing type in <b><u>ORDERING INFORMATION</u></b> | Apr.17.2009       |



## LY615128

Rev. 1.2

5V 512K X 8 BIT HIGH SPEED CMOS SRAM

### FEATURES

- Fast access time : 10/12/15ns
- Low power consumption:  
Operating current: 200/180/150mA (TYP.)  
Standby current: 1mA (TYP.)
- Single 5V power supply
- All inputs and outputs TTL compatible
- Fully static operation
- Tri-state output
- Data retention voltage : 2.0V (MIN.)
- **Green package available**
- Package : 44-pin 400 mil TSOP-II

### GENERAL DESCRIPTION

The LY615128 is a 4,194,304-bit low power CMOS static random access memory organized as 524,288 words by 8 bits. It is fabricated using very high performance, high reliability CMOS technology. Its standby current is stable within the range of operating temperature.

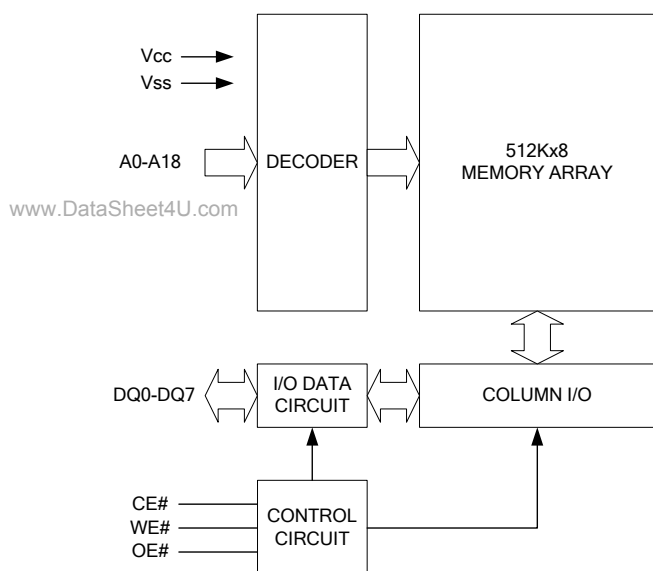
The LY615128 is well designed for low power application, and particularly well suited for battery back-up nonvolatile memory application.

The LY615128 operates from a single power supply of 5V and all inputs and outputs are fully TTL compatible

### PRODUCT FAMILY

| Product Family | Operating Temperature | Vcc Range  | Speed       | Power Dissipation               |                                  |
|----------------|-----------------------|------------|-------------|---------------------------------|----------------------------------|
|                |                       |            |             | Standby(I <sub>SB1</sub> ,TYP.) | Operating(I <sub>CC</sub> ,TYP.) |
| LY615128       | 0 ~ 70°C              | 4.5 ~ 5.5V | 10/12/15 ns | 1mA                             | 200/180/150mA                    |

### FUNCTIONAL BLOCK DIAGRAM



### PIN DESCRIPTION

| SYMBOL    | DESCRIPTION         |
|-----------|---------------------|
| A0 - A18  | Address Inputs      |
| DQ0 - DQ7 | Data Inputs/Outputs |
| CE#       | Chip Enable Inputs  |
| WE#       | Write Enable Input  |
| OE#       | Output Enable Input |
| Vcc       | Power Supply        |
| Vss       | Ground              |
| NC        | No Connection       |

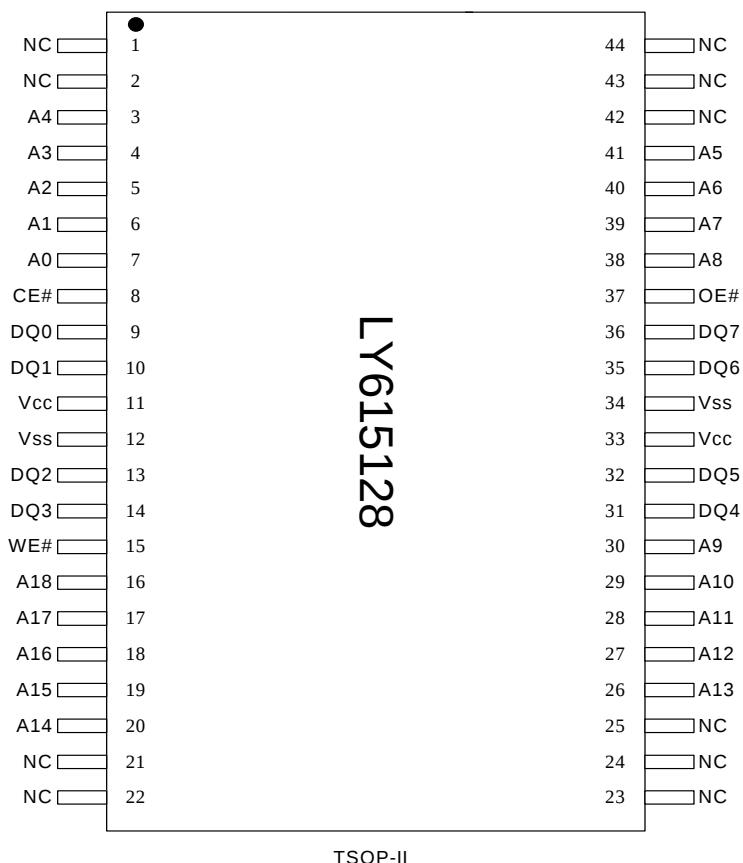


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### PIN CONFIGURATION

[www.DataSheet4U.com](http://www.DataSheet4U.com)

### ABSOLUTE MAXIMUM RATINGS\*

| PARAMETER                                | SYMBOL           | RATING           | UNIT |
|------------------------------------------|------------------|------------------|------|
| Voltage on Vcc relative to Vss           | V <sub>T1</sub>  | -0.5 to 4.6      | V    |
| Voltage on any other pin relative to Vss | V <sub>T2</sub>  | -0.5 to Vcc+0.5  | V    |
| Operating Temperature                    | T <sub>A</sub>   | 0 to 70(C grade) | °C   |
| Storage Temperature                      | T <sub>STG</sub> | -65 to 150       | °C   |
| Power Dissipation                        | P <sub>D</sub>   | 1                | W    |
| DC Output Current                        | I <sub>OUT</sub> | 50               | mA   |

\*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.



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### TRUTH TABLE

| MODE           | CE# | OE# | WE# | I/O OPERATION | SUPPLY CURRENT    |
|----------------|-----|-----|-----|---------------|-------------------|
| Standby        | H   | X   | X   | High-Z        | $I_{SB}, I_{SB1}$ |
| Output Disable | L   | H   | H   | High-Z        | $I_{CC}$          |
| Read           | L   | L   | H   | DOUT          | $I_{CC}$          |
| Write          | L   | X   | L   | DIN           | $I_{CC}$          |

 Note: H =  $V_{IH}$ , L =  $V_{IL}$ , X = Don't care.

### DC ELECTRICAL CHARACTERISTICS

| PARAMETER                              | SYMBOL        | TEST CONDITION                                                | MIN.  | TYP. <sup>4</sup> | MAX.         | UNIT    |
|----------------------------------------|---------------|---------------------------------------------------------------|-------|-------------------|--------------|---------|
| Supply Voltage                         | $V_{CC}$      |                                                               | 4.5   | 5.0               | 5.5          | V       |
| Input High Voltage                     | $V_{IH}^{*1}$ |                                                               | 2.2   | -                 | $V_{CC}+0.3$ | V       |
| Input Low Voltage                      | $V_{IL}^{*2}$ |                                                               | - 0.3 | -                 | 0.6          | V       |
| Input Leakage Current                  | $I_{LI}$      | $V_{CC} \geq V_{IN} \geq V_{SS}$                              | - 1   | -                 | 1            | $\mu A$ |
| Output Leakage Current                 | $I_{LO}$      | $V_{CC} \geq V_{OUT} \geq V_{SS}$ ,<br>Output Disabled        | - 1   | -                 | 1            | $\mu A$ |
| Output High Voltage                    | $V_{OH}$      | $I_{OH} = -4mA$                                               | 2.4   | -                 | -            | V       |
| Output Low Voltage                     | $V_{OL}$      | $I_{OL} = 8mA$                                                | -     | -                 | 0.4          | V       |
| Average Operating Power supply Current | $I_{CC}$      | Cycle time = Min.                                             | -10   | -                 | 220          | mA      |
|                                        |               | CE# = $V_{IL}$ , $I_{I/O} = 0mA$                              | -12   | -                 | 200          | mA      |
|                                        |               | Others at $V_{IL}$ or $V_{IH}$                                | -15   | -                 | 180          | mA      |
| Standby Power Supply Current           | $I_{SB}$      | CE# = $V_{IH}$ , others at $V_{IL}$ or $V_{IH}$               | -     | 5                 | 50           | mA      |
|                                        | $I_{SB1}$     | CE# $\geq V_{CC} - 0.2V$<br>Others at 0.2V or $V_{CC} - 0.2V$ | -     | 1                 | $10^{*5}$    | mA      |

Notes:

 1.  $V_{IH(max)} = V_{CC} + 3.0V$  for pulse width less than 10ns.

 2.  $V_{IL(min)} = V_{SS} - 3.0V$  for pulse width less than 10ns.

3. Over/Undershoot specifications are characterized, not 100% tested.

4. Typical values are included for reference only and are not guaranteed or tested.

 Typical values are measured at  $V_{CC} = V_{CC(TYP.)}$  and  $T_A = 25^\circ C$ 

5. 1mA for special request

### CAPACITANCE ( $T_A = 25^\circ C$ , $f = 1.0MHz$ )

| PARAMETER                | SYMBOL    | MIN. | MAX | UNIT |
|--------------------------|-----------|------|-----|------|
| Input Capacitance        | $C_{IN}$  | -    | 8   | pF   |
| Input/Output Capacitance | $C_{I/O}$ | -    | 10  | pF   |

Note : These parameters are guaranteed by device characterization, but not production tested.

**LY615128**

Rev. 1.2

**5V 512K X 8 BIT HIGH SPEED CMOS SRAM****AC TEST CONDITIONS**

|                                          |                                                   |
|------------------------------------------|---------------------------------------------------|
| Input Pulse Levels                       | 0.2V to $V_{CC} - 0.2V$                           |
| Input Rise and Fall Times                | 3ns                                               |
| Input and Output Timing Reference Levels | 1.5V                                              |
| Output Load                              | $C_L = 30pF + 1TTL$ , $I_{OH}/I_{OL} = -8mA/16mA$ |

**AC ELECTRICAL CHARACTERISTICS****(1) READ CYCLE**

| PARAMETER                          | SYM.        | LY615128-10 |      | LY615128-12 |      | LY615128-15 |      | UNIT |
|------------------------------------|-------------|-------------|------|-------------|------|-------------|------|------|
|                                    |             | MIN.        | MAX. | MIN.        | MAX. | MIN.        | MAX. |      |
| Read Cycle Time                    | $t_{RC}$    | 10          | -    | 12          | -    | 15          | -    | ns   |
| Address Access Time                | $t_{AA}$    | -           | 10   | -           | 12   | -           | 15   | ns   |
| Chip Enable Access Time            | $t_{ACE}$   | -           | 10   | -           | 12   | -           | 15   | ns   |
| Output Enable Access Time          | $t_{OE}$    | -           | 5    | -           | 6    | -           | 7    | ns   |
| Chip Enable to Output in Low-Z     | $t_{CLZ}^*$ | 2           | -    | 3           | -    | 4           | -    | ns   |
| Output Enable to Output in Low-Z   | $t_{OLZ}^*$ | 0           | -    | 0           | -    | 0           | -    | ns   |
| Chip Disable to Output in High-Z   | $t_{CHZ}^*$ | -           | 5    | -           | 6    | -           | 7    | ns   |
| Output Disable to Output in High-Z | $t_{OHZ}^*$ | -           | 5    | -           | 6    | -           | 7    | ns   |
| Output Hold from Address Change    | $t_{OH}$    | 3           | -    | 3           | -    | 3           | -    | ns   |

**(2) WRITE CYCLE**

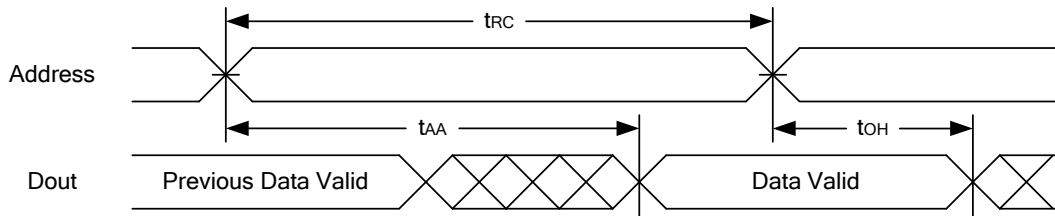
| PARAMETER                        | SYM.        | LY615128-10 |      | LY615128-12 |      | LY615128-15 |      | UNIT |
|----------------------------------|-------------|-------------|------|-------------|------|-------------|------|------|
|                                  |             | MIN.        | MAX. | MIN.        | MAX. | MIN.        | MAX. |      |
| Write Cycle Time                 | $t_{WC}$    | 10          | -    | 12          | -    | 15          | -    | ns   |
| Address Valid to End of Write    | $t_{AW}$    | 8           | -    | 10          | -    | 12          | -    | ns   |
| Chip Enable to End of Write      | $t_{CW}$    | 8           | -    | 10          | -    | 12          | -    | ns   |
| Address Set-up Time              | $t_{AS}$    | 0           | -    | 0           | -    | 0           | -    | ns   |
| Write Pulse Width                | $t_{WP}$    | 8           | -    | 9           | -    | 10          | -    | ns   |
| Write Recovery Time              | $t_{WR}$    | 0           | -    | 0           | -    | 0           | -    | ns   |
| Data to Write Time Overlap       | $t_{DW}$    | 6           | -    | 7           | -    | 8           | -    | ns   |
| Data Hold from End of Write Time | $t_{DH}$    | 0           | -    | 0           | -    | 0           | -    | ns   |
| Output Active from End of Write  | $t_{OW}^*$  | 2           | -    | 3           | -    | 4           | -    | ns   |
| Write to Output in High-Z        | $t_{WHZ}^*$ | -           | 6    | -           | 7    | -           | 8    | ns   |

\*These parameters are guaranteed by device characterization, but not production tested.

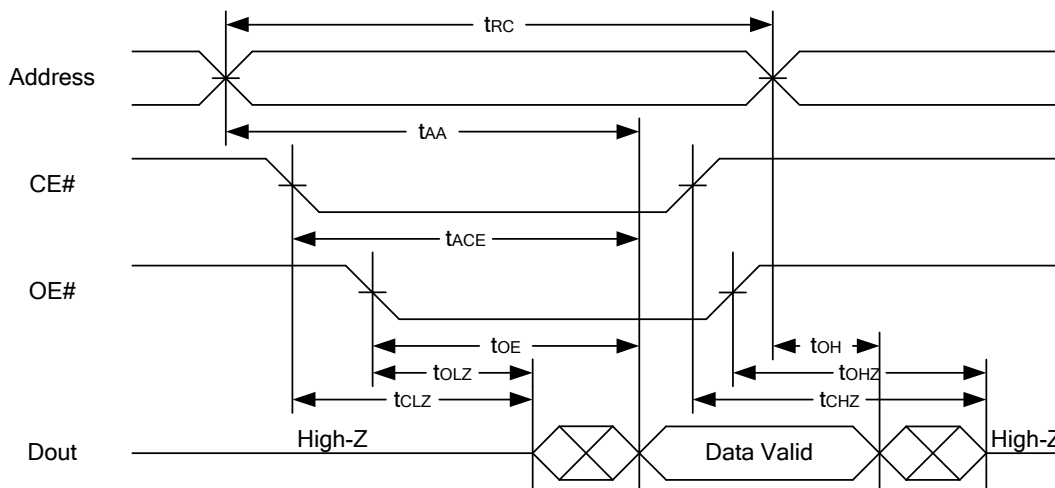


#### TIMING WAVEFORMS

##### READ CYCLE 1 (Address Controlled) (1,2)



##### READ CYCLE 2 (CE# and OE# Controlled) (1,3,4,5)

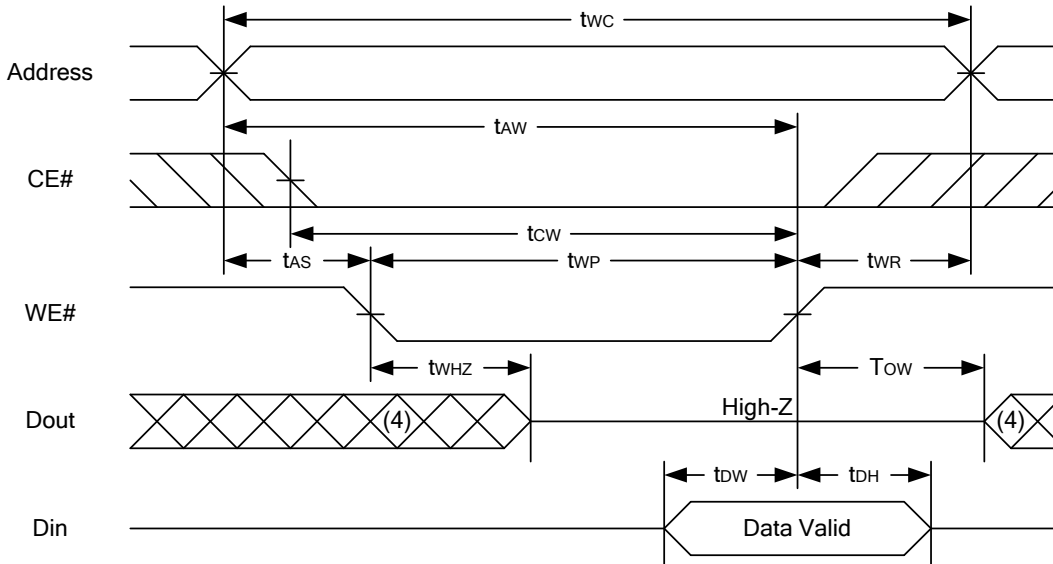


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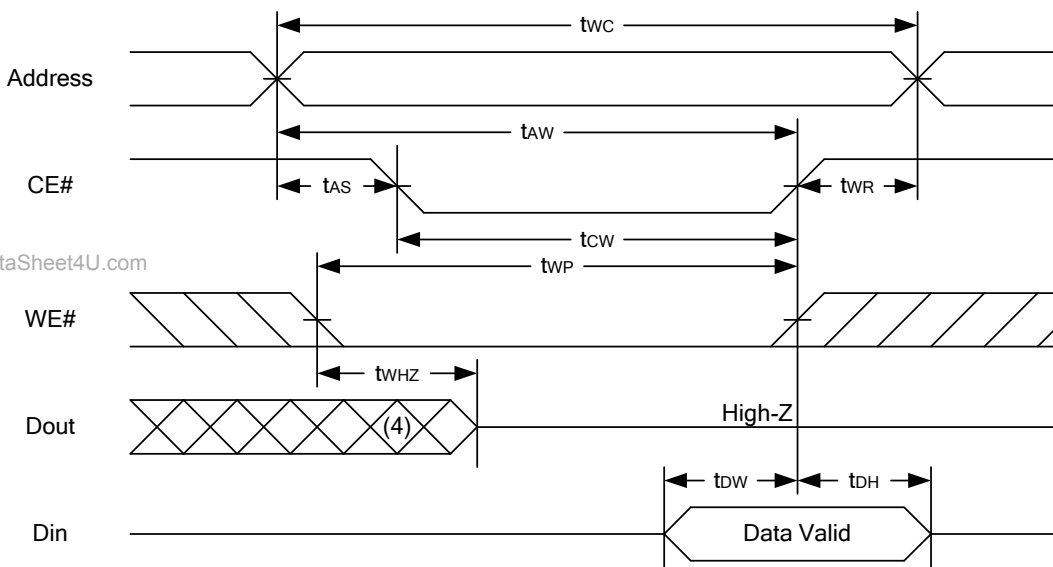
#### Notes :

1. WE# is high for read cycle.
2. Device is continuously selected OE# = low, CE# = low.
3. Address must be valid prior to or coincident with CE# = low; otherwise tAA is the limiting parameter.
4. tCLZ, tOLZ, tCHZ and tOHZ are specified with CL = 5pF. Transition is measured  $\pm 500\text{mV}$  from steady state.
5. At any given temperature and voltage condition, tCHZ is less than tCLZ, tOHZ is less than tOLZ.

#### WRITE CYCLE 1 (WE# Controlled) (1,2,3,5,6)



#### WRITE CYCLE 2 (CE# Controlled) (1,2,5,6)



#### Notes :

1. WE#, CE# must be high during all address transitions.
2. A write occurs during the overlap of a low CE#, low WE#.
3. During a WE# controlled write cycle with OE# low, tWP must be greater than tWHZ + tDW to allow the drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the CE# low transition occurs simultaneously with or after WE# low transition, the outputs remain in a high impedance state.
6. tow and twhz are specified with CL = 5pF. Transition is measured  $\pm 500\text{mV}$  from steady state.

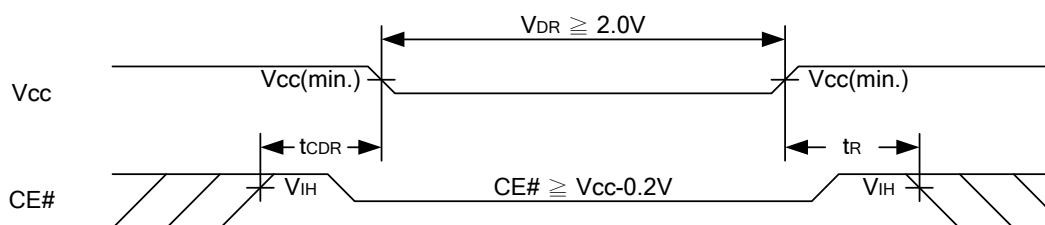


#### DATA RETENTION CHARACTERISTICS

| PARAMETER                           | SYMBOL           | TEST CONDITION                                                                                          | MIN.              | TYP. | MAX. | UNIT |
|-------------------------------------|------------------|---------------------------------------------------------------------------------------------------------|-------------------|------|------|------|
| V <sub>CC</sub> for Data Retention  | V <sub>DR</sub>  | CE# $\geq$ V <sub>CC</sub> - 0.2V                                                                       | 2.0               | -    | 5.5  | V    |
| Data Retention Current              | I <sub>DR</sub>  | V <sub>CC</sub> = 2.0V<br>CE# $\geq$ V <sub>CC</sub> - 0.2V<br>Others at 0.2V or V <sub>CC</sub> - 0.2V | -                 | 0.5  | 1    | mA   |
| Chip Disable to Data Retention Time | t <sub>CDR</sub> | See Data Retention Waveforms (below)                                                                    | 0                 | -    | -    | ns   |
| Recovery Time                       | t <sub>R</sub>   |                                                                                                         | t <sub>RC</sub> * | -    | -    | ns   |

t<sub>RC</sub>\* = Read Cycle Time

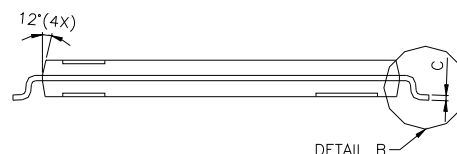
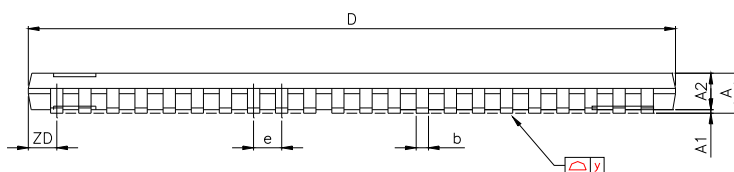
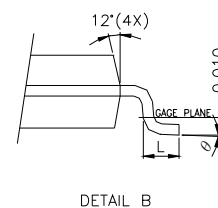
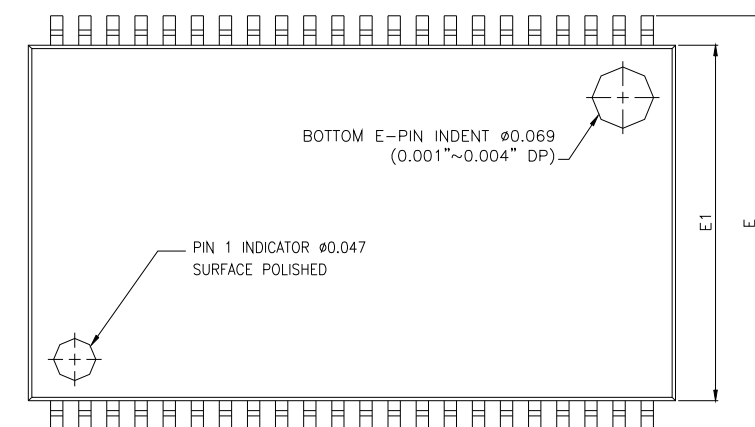
#### DATA RETENTION WAVEFORM





#### PACKAGE OUTLINE DIMENSION

##### 44-pin 400mil TSOP-II Package Outline Dimension



| SYMBOLS | DIMENSIONS IN MILLMETERS |        |        | DIMENSIONS IN MILS |      |      |
|---------|--------------------------|--------|--------|--------------------|------|------|
|         | MIN.                     | NOM.   | MAX.   | MIN.               | NOM. | MAX. |
| A       | -                        | -      | 1.20   | -                  | -    | 47.2 |
| A1      | 0.05                     | 0.10   | 0.15   | 2.0                | 3.9  | 5.9  |
| A2      | 0.95                     | 1.00   | 1.05   | 37.4               | 39.4 | 41.3 |
| b       | 0.30                     | -      | 0.45   | 11.8               | -    | 17.7 |
| c       | 0.12                     | -      | 0.21   | 4.7                | -    | 8.3  |
| D       | 18.212                   | 18.415 | 18.618 | 717                | 725  | 733  |
| E       | 11.506                   | 11.760 | 12.014 | 453                | 463  | 473  |
| E1      | 9.957                    | 10.160 | 10.363 | 392                | 400  | 408  |
| e       | -                        | 0.800  | -      | -                  | 31.5 | -    |
| L       | 0.40                     | 0.50   | 0.60   | 15.7               | 19.7 | 23.6 |
| ZD      | -                        | 0.805  | -      | -                  | 31.7 | -    |
| y       | -                        | -      | 0.076  | -                  | -    | 3    |
| θ       | 0°                       | 3°     | 6°     | 0°                 | 3°   | 6°   |



#### ORDERING INFORMATION

LY615128 U V - WW Y Z

Z : Packing Type

Blank : Tube or Tray

T : Tape Reel

Y : Temperature Range

Blank : (Commercial) 0°C ~ 70°C

WW : Access Time(Speed)

V : Lead Information

L : Green Package

U : Package Type

M : 44-pin 400 mil TSOP-II



**Lyontek Inc.**

**LY615128**

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